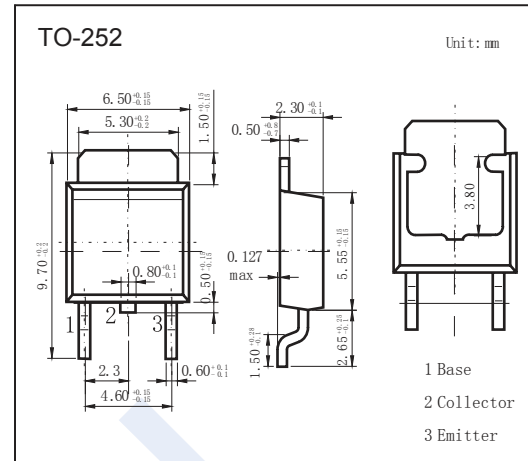


## PNP Transistors

## 2SB768

## ■ Features

- High voltage:  $V_{CEO} = -150V$
- Complimentary to 2SD1033.

■ Absolute Maximum Ratings  $T_a = 25^\circ C$ 

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CBO}$	-200	V
Collector - Emitter Voltage	$V_{CEO}$	-150	
Emitter - Base Voltage	$V_{EBO}$	-5	
Collector Current - Continuous	$I_C$	-2	A
Collector Current - Pulse (Note.1)	$I_{CP}$	-3	
Collector Power Dissipation	$P_C$	2	W
Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature range	$T_{stg}$	-55 to 150	

Note.1:  $PW \leq 10$  ms, Duty Cycle  $\leq 50\%$ .

■ Electrical Characteristics  $T_a = 25^\circ C$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CBO}$	$I_C = -100 \mu A, I_E = 0$	-200			V
Collector- emitter breakdown voltage	$V_{CEO}$	$I_C = -1$ mA, $I_B = 0$	-150			
Emitter - base breakdown voltage	$V_{EBO}$	$I_E = -100 \mu A, I_C = 0$	-5			
Collector-base cut-off current	$I_{CBO}$	$V_{CB} = -150$ V, $I_E = 0$			-50	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -4$ V, $I_C = 0$			-50	
Collector-emitter saturation voltage (Note.1)	$V_{CE(sat)}$	$I_C = -500$ mA, $I_B = -50$ mA		-0.15	-1	V
Base - emitter saturation voltage (Note.1)	$V_{BE(sat)}$	$I_C = -500$ mA, $I_B = -50$ mA			-1.2	
DC current gain (Note.1)	$h_{FE}$	$V_{CE} = -10$ V, $I_C = -400$ mA	40	80	200	
Transition frequency	$f_T$	$V_{CE} = -10$ V, $I_E = 0.4$ mA		10		MHz

Note.1: Pulse test : Pulse width  $\leq 350 \mu s$ , Duty Cycle  $\leq 2\%$ .

■ Classification of  $h_{FE}$ 

Type	2SB768-M	2SB768-L	2SB768-K
Range	40-80	60-120	100-200

# PNP Transistors

## 2SB768

■ Typical Characteristics

